1200–1600 MHz GaN MMIC Power Amplifier Die

LCI-PA-1200-1600-PS43p5T is a GaN MMIC power amplifier supplied as bare die for 1200–1600 MHz. It supports CW and pulsed operation.

The RF table specifies: Saturated output power: 43.5 dBm (typical); Power gain: 17 dB (typical); Power-added efficiency: 60 % (typical). RF test conditions: TA = +25 °C; Vd = +28 V; Vg = -2.8 V. Die dimensions: 2.7 × 2 × 0.1 mm.



RF characteristics

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Operating frequency	f	1200	-	1600	MHz
Saturated output power	Psat	-	43.5	-	dBm
Power gain	Gp	-	17	-	dB
Power-gain flatness	ΔGp	-	-	±0.5	dB
Power-added efficiency	PAE	-	60	-	%
Small-signal gain	S21	-	25	-	dB
Small-signal gain flatness	ΔS21	-	-	±0.5	dB
Input VSWR	VSWR(in)	-	1.3	1.4	-

DC bias and current

TA = +25 °C

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Drain voltage	Vd	-	28	32	V
Gate voltage	Vg	-3	-2.6	-2.4	V
Quiescent drain current	Id	-	0.9	-	A
Dynamic drain current	Idd	-	1.4	1.5	A
Dynamic gate current	Igg	-	0.2	1	mA

Absolute limits

Absolute limits; these are not normal operating targets.

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum drain-source voltage	Vd	-	-	32	V
Minimum gate bias	Vg	-5	-	-	V
Maximum input power	Pin	-	-	30	dBm
Maximum channel temperature	Top	-	-	225	°C
Storage temperature	TSTG	-65	-	150	°C

Die dimensions

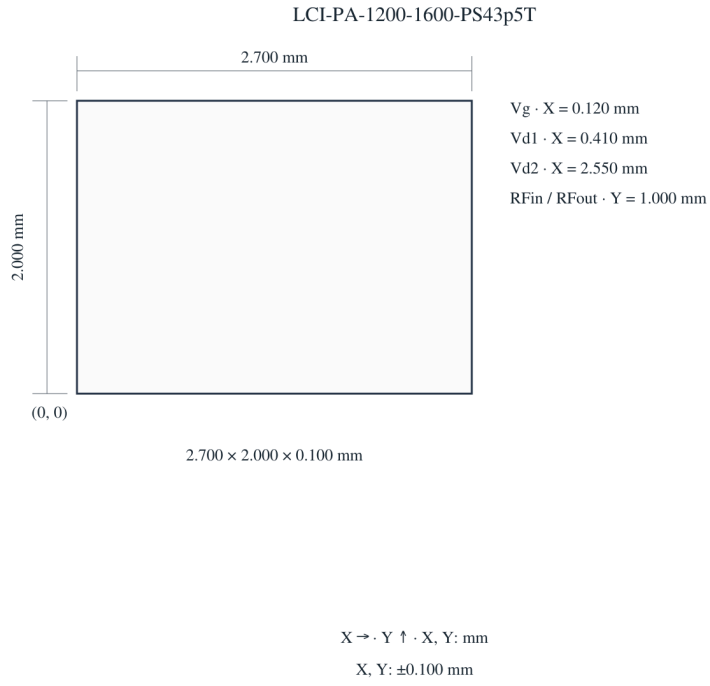
Parameter	Value	Unit
Die dimensions	2.7 × 2 × 0.1	mm
Plan-view outline tolerance	±100 (Plan-view outline only; the source does not specify thickness tolerance.)	µm

Current publication record · 1.7 · 2026-11-12. Product description or editorial content updated. Replaces revision 1.6.

Die integration and bias sequencing

Apply gate bias before drain bias at power-up. At power-down, remove drain bias before gate bias. Use clean handling, ESD protection and a carrier with thermal expansion compatible with the SiC die. Outline and dimensioned coordinates in mm. Use this drawing as a dimensional reference. Fabrication and wire bonding require complete drawings.

Mechanical Outline

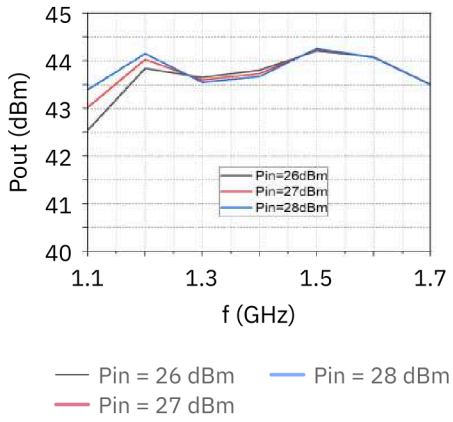


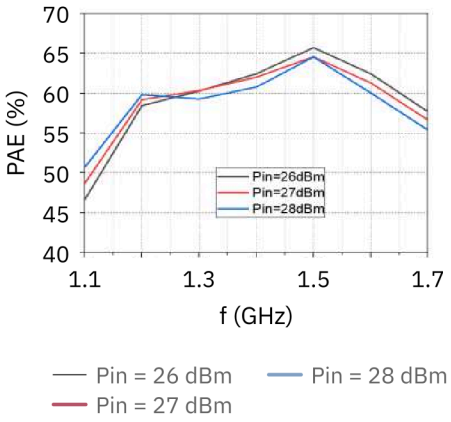
Performance curves

Read each figure with its stated operating conditions.

Pulsed — Saturated output power; Power-added efficiency; Dynamic drain current; Input matching; Gain.

Figure notes: TA = +25°C; Vd=+28V; Vg=-2.6V. τ = 100 µs; D = 10%. Conditions apply to the indicated plots and their own legends.





Pin = 26 dBm Pin = 28 dBm
Pin = 27 dBm

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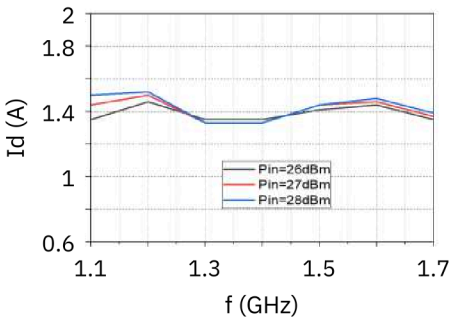

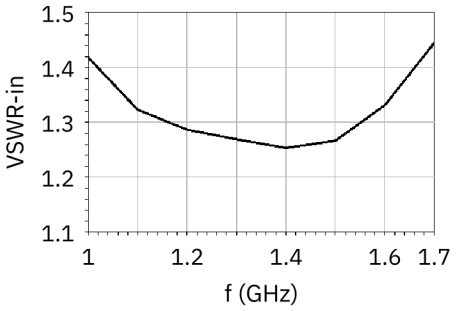

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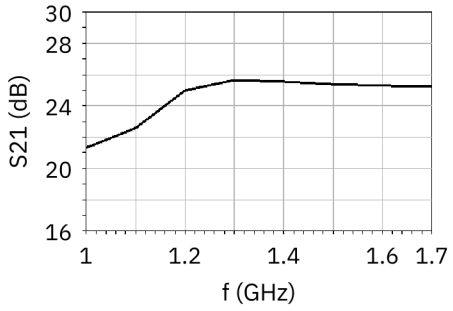
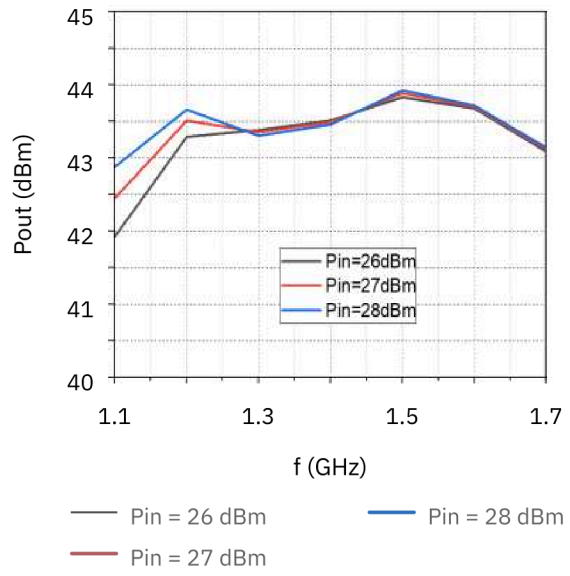
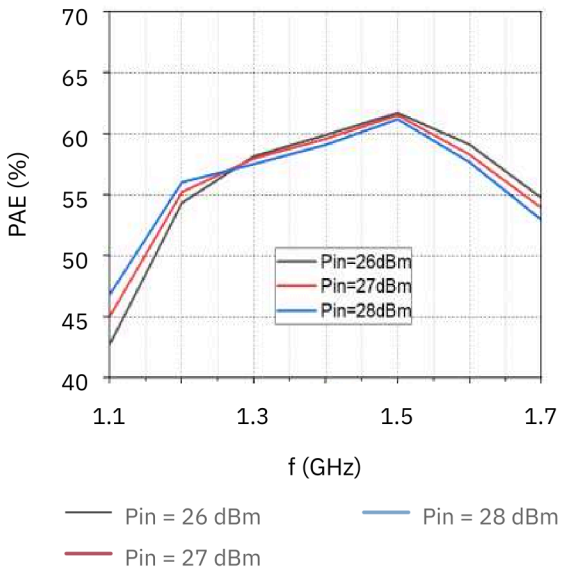
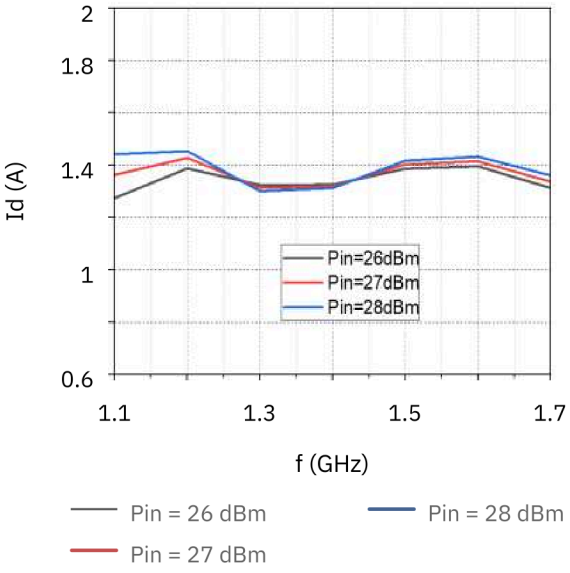


Continuous wave (CW) — Saturated output power; Power-added efficiency; Dynamic drain current.

Figure notes: TA = +25°C; Vd=+28V; Vg=-2.6V.







Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.